

PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI IGBT CY25AAJ-8

Nch IGBT for STROBE FLASHER

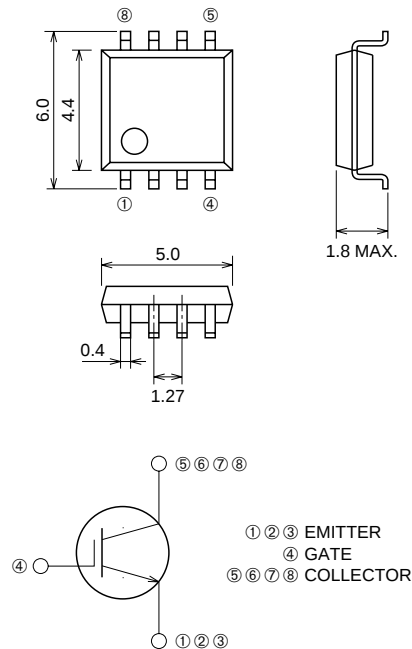
CY25AAJ-8



- V_{CES} 400V
- I_{CM} 150A
- Drive voltage 4V

OUTLINE DRAWING

Dimensions in mm



SOP-8

APPLICATION

Strobe Flasher for camera

MAXIMUM RATINGS (Tc = 25°C)

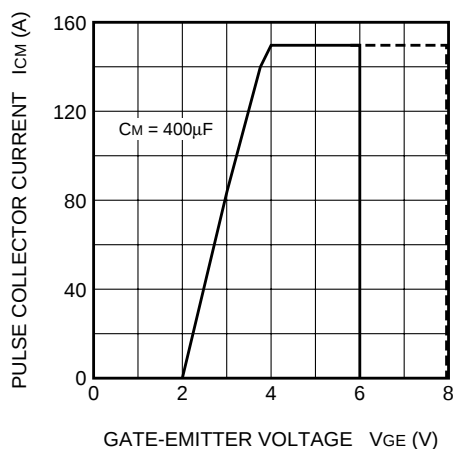
Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V$	400	V
V_{GES}	Gate-emitter voltage	$V_{CE} = 0V$	± 6	V
V_{GEM}	Peak gate-emitter voltage	$V_{CE} = 0V, t_w = 10s$	± 8	V
I_{CM}	Collector current (Pulsed)	$C_M = 400\mu F$ see figure1	150	A
T_j	Junction temperature		-40 ~ +150	°C
T_{stg}	Storage temperature		-40 ~ +150	°C

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ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$I_C = 1\text{mA}$, $V_{GE} = 0\text{V}$	450	—	—	V
I_{CES}	Collector-emitter leakage current	$V_{CE} = 400\text{V}$, $V_{GE} = 0\text{V}$	—	—	10	μA
I_{GES}	Gate-emitter leakage current	$V_{GE} = \pm 6\text{V}$, $V_{CE} = 0\text{V}$	—	—	± 0.1	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{CE} = 10\text{V}$, $I_C = 1\text{mA}$	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE

